High-temperature 60 V, 1 A Schottky barrier rectifier

10 October 2012

Product data sheet

# 1. Product profile

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD123W small and flat lead Surface-Mounted Device (SMD) plastic package.

### **1.2 Features and benefits**

- Average forward current:  $I_{F(AV)} \le 1 A$
- Reverse voltage:  $V_R \le 60 V$
- Low forward voltage
- High power capability due to clip-bonding technology
- Small and flat lead SMD plastic package
- AEC-Q101 qualified
- High temperature T<sub>i</sub> ≤ 175 °C

### **1.3 Applications**

Quick reference data

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection

## 1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
l <sub>F</sub>	forward current	T <sub>sp</sub> = 165 °C		-	-	1.4	А
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; f = 20 kHz; T <sub>amb</sub> ≤ 140 °C; square wave	[1]	-	-	1	A
		$\delta$ = 0.5 ; f = 20 kHz; T <sub>sp</sub> ≤ 170 °C; square wave		-	-	1	A
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	-	60	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 1 A; T <sub>j</sub> = 25 °C		-	460	530	mV
I <sub>R</sub>	reverse current	$\label{eq:tau} \begin{array}{l} T_{j} = 25 \ ^{\circ}C; \ V_{R} = 60 \ V; \ t_{p} \leq 300 \ \mu s; \\ \delta \leq 0.02 \ ; \ pulsed \end{array}$		-	30	60	μA



Table 1.



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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t <sub>rr</sub>	reverse recovery time	$I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$	-	4.4	-	ns

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode[1]	1 2	1 🕂 2
2	A	anode	SOD123W	sym001

[1] The marking bar indicates the cathode.

# 3. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
PMEG6010ETR	SOD123W	plastic surface mounted package; 2 leads	SOD123W					

# 4. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG6010ETR	EK

# 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	60	V
l <sub>F</sub>	forward current	T <sub>sp</sub> = 165 °C		-	1.4	А
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; f = 20 kHz; T <sub>amb</sub> ≤ 140 °C; square wave	[1]	-	1	A
		$\delta$ = 0.5 ; f = 20 kHz; T <sub>sp</sub> ≤ 170 °C; square wave		-	1	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	50	A

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Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	680	mW
		[3]	-	1150	mW	
			[1]	-	2140	mW
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

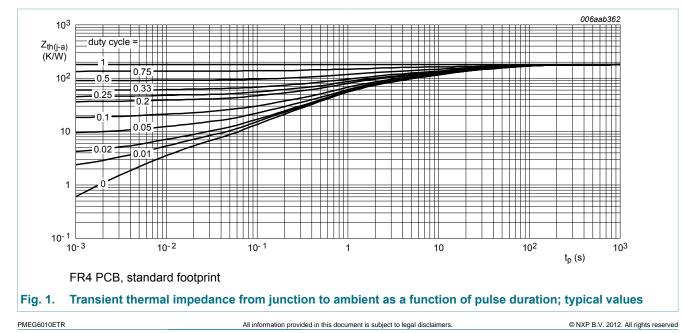
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

## 6. Thermal characteristics

Table 6. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1][2]	-	-	220	K/W	
	from junction to ambient		[1][3]	-	-	130	K/W	
	ampient		[1][4]	-	-	70	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	18	K/W	

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.

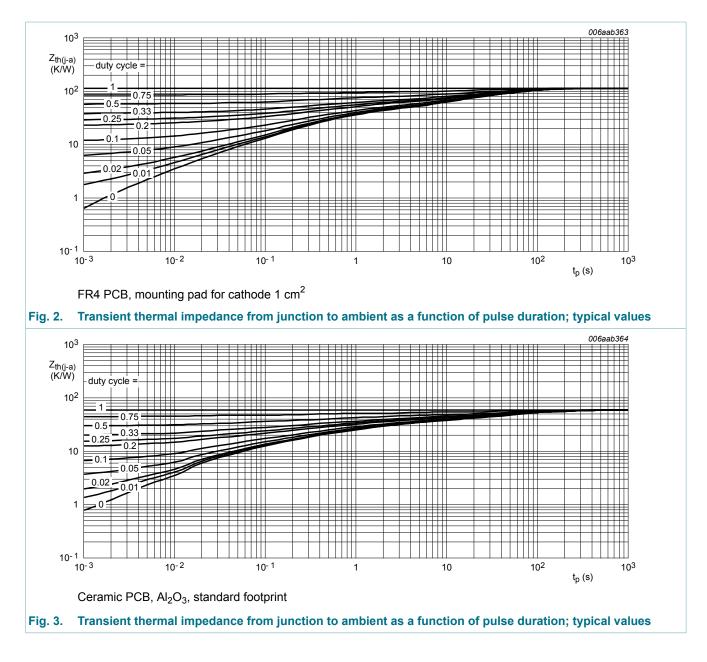
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of cathode tab.



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# 7. Characteristics

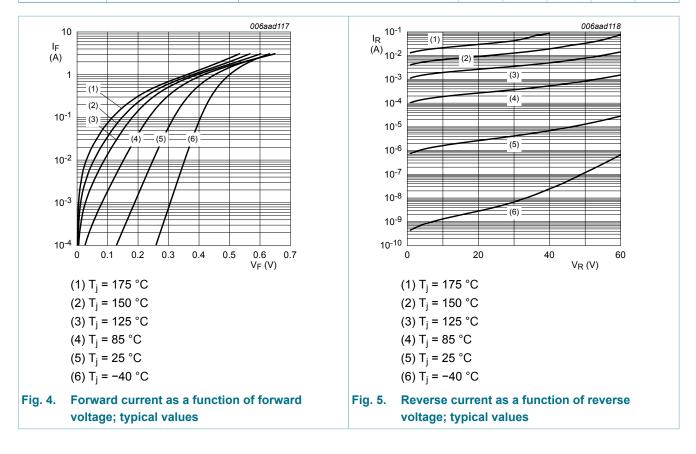
Table 7. Characteristics								
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 0.1 A; T <sub>j</sub> = 25 °C		-	320	370	mV	
		I <sub>F</sub> = 0.7 A; T <sub>j</sub> = 25 °C		-	430	490	mV	
		I <sub>F</sub> = 1 A; T <sub>j</sub> = 25 °C		-	460	530	mV	
		I <sub>F</sub> = 1 A; T <sub>j</sub> = -40 °C		-	510	590	mV	
		I <sub>F</sub> = 1 A; T <sub>j</sub> = 125 °C		-	400	480	mV	
		I <sub>F</sub> = 1 A; T <sub>j</sub> = 150 °C		-	380	460	mV	
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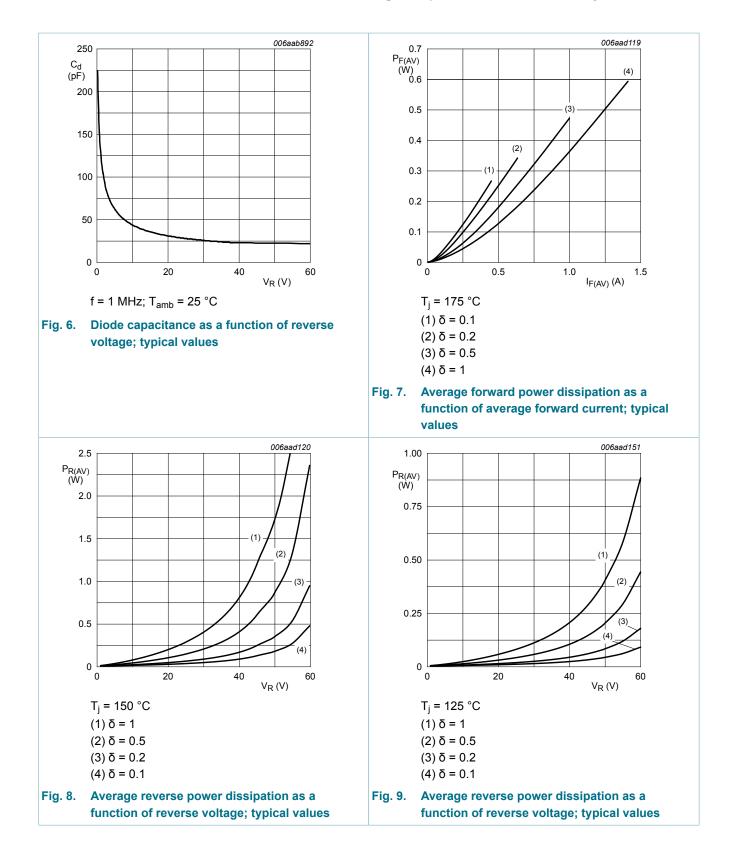
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I <sub>F</sub> = 1 A; T <sub>j</sub> = 175 °C	-	365	450	mV
I <sub>R</sub>	reverse current	$V_R$ = 5 V; T <sub>j</sub> = 25 °C; t <sub>p</sub> ≤ 300 µs; $\delta \le 0.02$ ; pulsed	-	1.2	-	μA
		$V_R$ = 10 V; T <sub>j</sub> = 25 °C; t <sub>p</sub> ≤ 300 µs; $\bar{o} \le 0.02$ ; pulsed	-	1.7	-	μA
		$V_R$ = 60 V; T <sub>j</sub> = 25 °C; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02 ; pulsed	-	30	60	μA
		$V_R$ = 60 V; T <sub>j</sub> = -40 °C; t <sub>p</sub> ≤ 300 µs; $\overline{o} \le 0.02$ ; pulsed	-	0.6	10	μA
		$V_R$ = 60 V; T <sub>j</sub> = 125 °C; t <sub>p</sub> ≤ 300 µs; $\delta \le 0.02$ ; pulsed	-	14	50	mA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	120	-	pF
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	40	-	pF
t <sub>rr</sub>	reverse recovery time	$I_F$ = 0.5 A; $I_R$ = 0.5 A; $I_{R(meas)}$ = 0.1 A; T <sub>j</sub> = 25 °C	-	4.4	-	ns
V <sub>FRM</sub>	peak forward recovery voltage	I <sub>F</sub> = 1 A; dI <sub>F</sub> /dt = 40 A/μs; T <sub>j</sub> = 25 °C	-	500	-	mV



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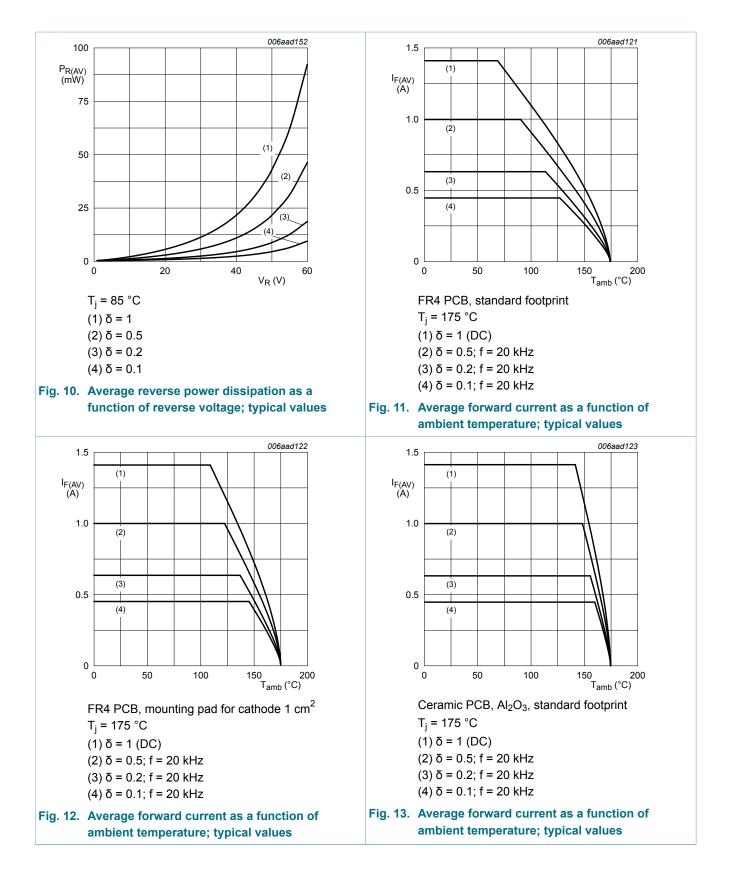
#### High-temperature 60 V, 1 A Schottky barrier rectifier



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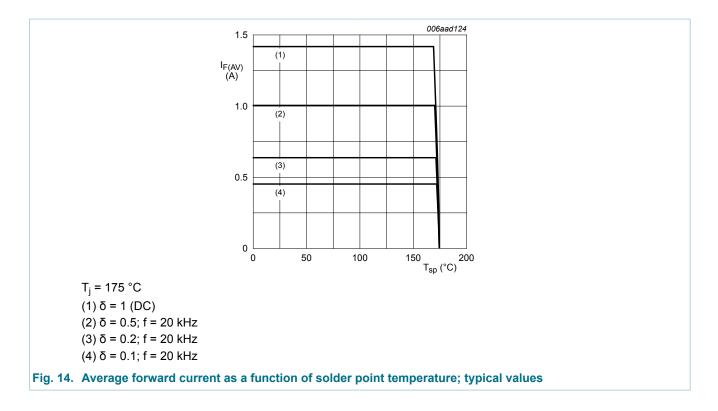
#### High-temperature 60 V, 1 A Schottky barrier rectifier



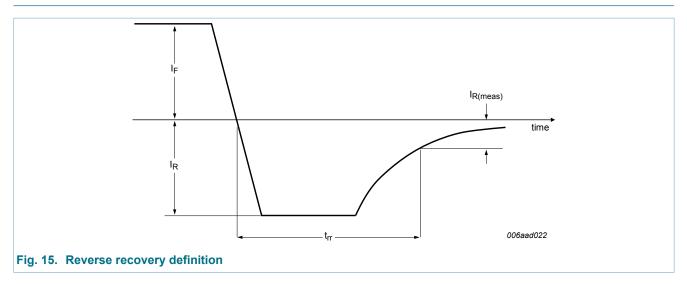
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# PMEG6010ETR

#### High-temperature 60 V, 1 A Schottky barrier rectifier

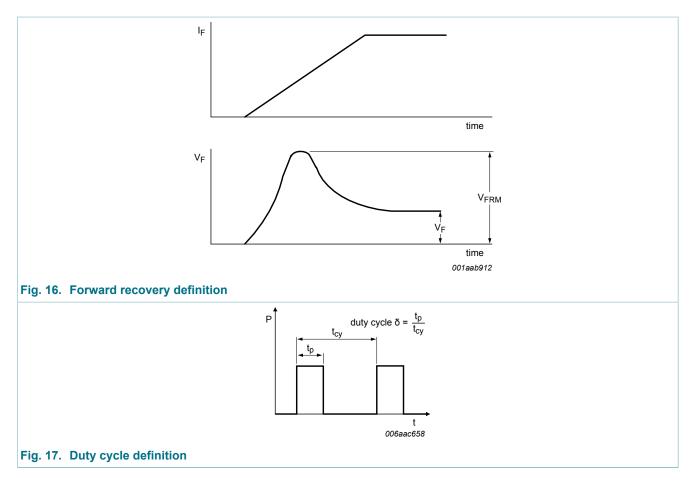


# 8. Test information



# PMEG6010ETR

#### High-temperature 60 V, 1 A Schottky barrier rectifier



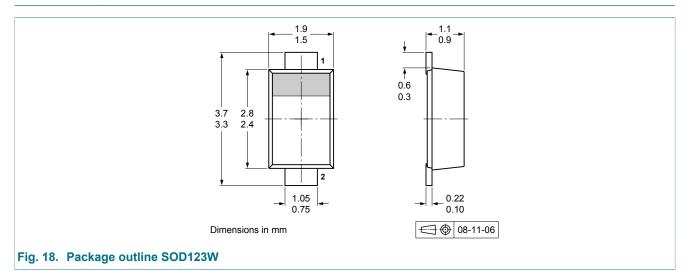
The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

#### 8.1 Quality information

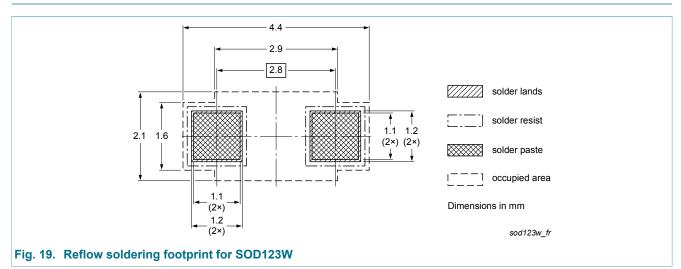
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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### 9. Package outline



# 10. Soldering



# 11. Revision history

Table 8. Revision history								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMEG6010ETR v.1	20121010	Product data sheet	-	-				

PMEG6010ETR

#### High-temperature 60 V, 1 A Schottky barrier rectifier

### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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